



STGP5NC60KD - STGF5NC60KD STGB5NC60KD

N-CHANNEL 5A - 600V - TO-220/TO-220FP/D²PAK
SHORT CIRCUIT RATED PowerMESH™ IGBT

TARGET SPECIFICATION

Table 1: General Features

TYPE	V _{CES}	V _{CE(sat)} (Max) @25°C	I _C @100°C
STGB5NC60KD	600 V	< 2.5 V	10 A
STGF5NC60KD	600 V	< 2.5 V	10 A
STGP5NC60KD	600 V	< 2.5 V	10 A

- OFF LOSSES INCLUDE TAIL CURRENT
- LOW ON-VOLTAGE DROP (V_{cesat})
- SHORT CIRCUIT RATED
- SWITCHING LOSSES INCLUDE DIODE RECOVERY ENERGY
- LOWER C_{RES} / C_{IES} RATIO

DESCRIPTION

Using the latest high voltage technology based on a patented strip layout, STMicroelectronics has designed an advanced family of IGBTs, the PowerMESH™ IGBTs, with outstanding performances. The suffix "K" identifies a family optimized for high frequency motor control applications with short circuit withstand capability.

APPLICATIONS

- HIGH FREQUENCY MOTOR CONTROLS
- SMPS and PFC IN BOTH HARD SWITCH AND RESONANT TOPOLOGIES
- MOTOR DRIVERS

Figure 1: Package

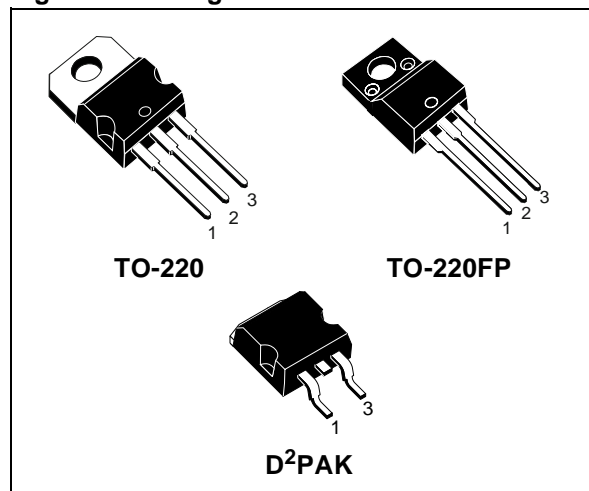


Figure 2: Internal Schematic Diagram

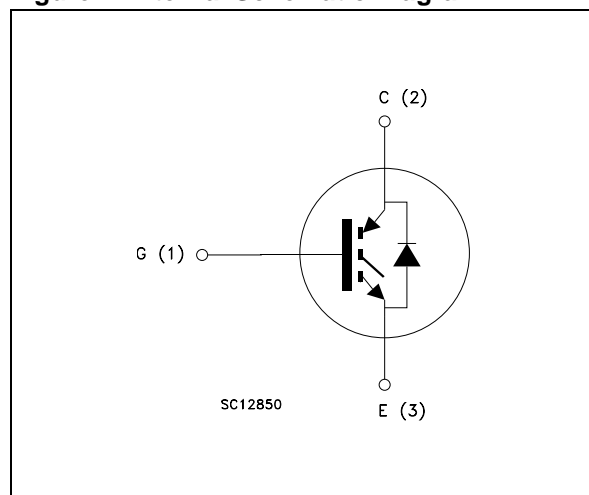


Table 2: Order Codes

SALES TYPE	MARKING	PACKAGE	PACKAGING
STGB5NC60KDT4	GB5NC60KD	D ² PAK	TAPE & REEL
STGF5NC60KD	GF5NC60KD	TO-220FP	TUBE
STGP5NC60KD	GP5NC60KD	TO-220	TUBE

Rev. 1

Table 3: Absolute Maximum ratings

Symbol	Parameter	Value		Unit
		STGB5NC60KD STGP5NC60KD	STGF5NC60KD	
V _{CES}	Collector-Emitter Voltage (V _{GS} = 0)	600		V
V _{ECR}	Emitter-Collector Voltage	20		V
V _{GE}	Gate-Emitter Voltage	±20		V
I _C	Collector Current (continuous) at T _C = 25°C (#)	20		A
I _C	Collector Current (continuous) at T _C = 100°C (#)	10		A
I _{CM} (■)	Collector Current (pulsed)	40		A
P _{TOT}	Total Dissipation at T _C = 25°C	60	25	W
	Derating Factor	0.48	0.20	W/°C
V _{ISO}	Insulation Withstand Voltage A.C.(t = 1 sec; T _c = 25°C)	--	2500	V
T _{stg}	Storage Temperature	– 55 to 150		°C
T _j	Operating Junction Temperature			

(■)Pulse width limited by max. junction temperature.

Table 4: Thermal Data

			Min.	Typ.	Max.	
R _{thj-case}	Thermal Resistance Junction-case	TO-220 D2PAK			2.08	°C/W
		TO-220FP			5.0	°C/W
R _{thj-amb}	Thermal Resistance Junction-ambient				62.5	°C/W
T _L	Maximum Lead Temperature for Soldering Purpose (1.6 mm from case, for 10 sec.)			300		°C

ELECTRICAL CHARACTERISTICS (T_{CASE} =25°C UNLESS OTHERWISE SPECIFIED)
Table 5: Main Parameters

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V _{BR(CES)}	Collector-Emitter Breakdown Voltage	I _C = 250 μA, V _{GE} = 0	600			V
I _{CES}	Collector cut-off Current (V _{GE} = 0)	V _{CE} = Max Rating, T _C = 25°C V _{CE} =Max Rating, T _C = 125°C			250 2	μA mA
I _{GES}	Gate-Emitter Leakage Current (V _{CE} = 0)	V _{GE} = ±20V , V _{CE} = 0			±250	nA
V _{GE(th)}	Gate Threshold Voltage	V _{CE} = V _{GE} , I _C = 250 μA	5		7	V
V _{CE(sat)}	Collector-Emitter Saturation Voltage	V _{GE} = 15V, I _C = 5A V _{GE} = 15V, I _C = 5A, T _c = 125°C		2 1.8	2.5	V V

(#) Calculated according to the iterative formula:

$$I_C(T_C) = \frac{T_{JMAX} - T_C}{R_{THJ-C} \times V_{CESAT(MAX)}(T_C, I_C)}$$

ELECTRICAL CHARACTERISTICS (CONTINUED)**Table 6: Dynamic**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$g_{fs}(1)$	Forward Transconductance	$V_{CE} = 15\text{ V}$, $I_C = 5\text{ A}$		15		S
C_{ies} C_{oes} C_{res}	Input Capacitance Output Capacitance Reverse Transfer Capacitance	$V_{CE} = 25\text{ V}$, $f = 1\text{ MHz}$, $V_{GE} = 0$		410 48 9		pF pF pF
Q_g Q_{ge} Q_{gc}	Total Gate Charge Gate-Emitter Charge Gate-Collector Charge	$V_{CE} = 390\text{ V}$, $I_C = 5\text{ A}$, $V_{GE} = 15\text{ V}$, (see Figure 5)		19 TBD TBD		nC nC nC
t_{scw}	Short Circuit Withstand Time	$V_{CE} = 0.5 V_{BR(CES)}$, $T_J = 125^\circ\text{C}$ $R_G = 10\ \Omega$, $V_{GE} = 15\text{ V}$	TBD			μs

(1) Pulsed: Pulse duration = 300 μs , duty cycle 1.5%**Table 7: Switching On**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r (di/dt) _{on} E _{on} (2)	Turn-on Delay Time Current Rise Time Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$ $R_G = 3.3\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 25^\circ\text{C}$ (see Figure 3)		TBD TBD TBD TBD		ns ns A/ μs μJ
$t_{d(on)}$ t_r (di/dt) _{on} E _{on} (2)	Turn-on Delay Time Current Rise Time Turn-on Current Slope Turn-on Switching Losses	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$ $R_G = 3.3\ \Omega$, $V_{GE} = 15\text{ V}$, $T_J = 125^\circ\text{C}$ (see Figure 3)		TBD TBD TBD TBD		ns ns A/ μs μJ

2) E_{on} is the turn-on losses when a typical diode is used in the test circuit in figure 2. If the IGBT is offered in a package with a co-pack diode, the co-pack diode is used as external diode. IGBTs & DIODE are at the same temperature (25°C and 125°C)**Table 8: Switching Off**

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$t_r(V_{off})$ $t_{d(off)}$ t_f E _{off} (3) E _{ts}	Off Voltage Rise Time Turn-off Delay Time Current Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_{GE} = 3.3\ \Omega$, $V_{GE} = 15\text{ V}$ $T_J = 25^\circ\text{C}$ (see Figure 3)		TBD TBD 75 TBD TBD		ns ns ns μJ μJ
$t_r(V_{off})$ $t_{d(off)}$ t_f E _{off} (3) E _{ts}	Off Voltage Rise Time Turn-off Delay Time Current Fall Time Turn-off Switching Loss Total Switching Loss	$V_{CC} = 390\text{ V}$, $I_C = 5\text{ A}$, $R_{GE} = 3.3\ \Omega$, $V_{GE} = 15\text{ V}$ $T_J = 125^\circ\text{C}$ (see Figure 3)		TBD TBD 110 TBD TBD		ns ns ns μJ μJ

(3) Turn-off losses include also the tail of the collector current.

Table 9: Collector-Emitter Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
I_f I_{fm}	Forward Current Forward Current Pulsed				7.5 12	A A
V_f	Forward On-Voltage	$I_f = 1.5\text{ A}$ $I_f = 1.5\text{ A}, T_j = 125\text{ °C}$		1.6 1.3	2.9	V V
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_f = 1.5\text{ A}, V_R = 30\text{ V},$ $T_j = 25\text{ °C}, di/dt = 100\text{ A}/\mu\text{s}$ (see Figure 6)		TBD TBD TBD		ns nC A
t_{rr} Q_{rr} I_{rrm}	Reverse Recovery Time Reverse Recovery Charge Reverse Recovery Current	$I_f = 1.5\text{ A}, V_R = 30\text{ V},$ $T_j = 125\text{ °C}, di/dt = 100\text{ A}/\mu\text{s}$ (see Figure 6)		TBD TBD TBD		ns nC A

Figure 3: Test Circuit for Inductive Load Switching

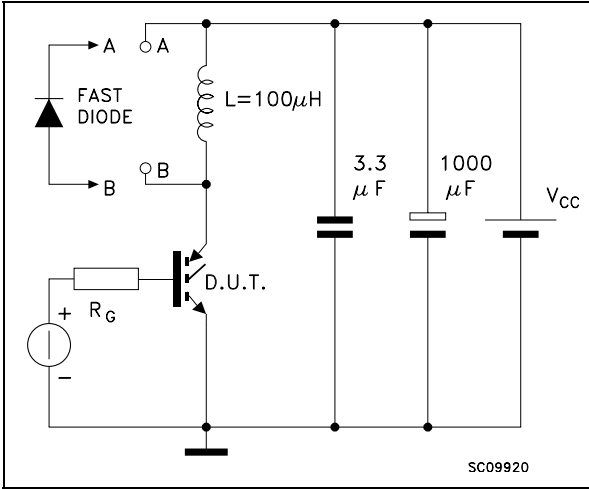


Figure 4: Switching Waveforms

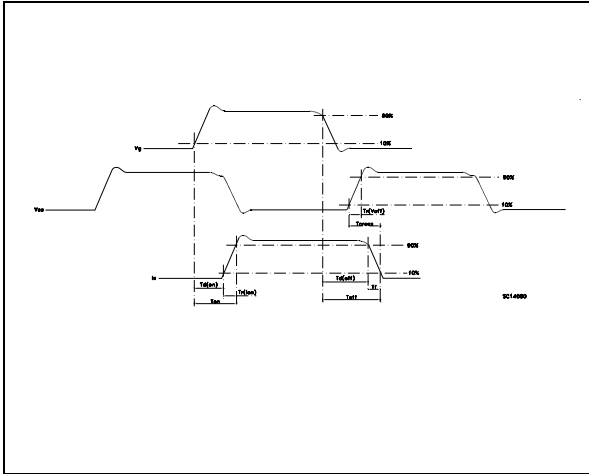
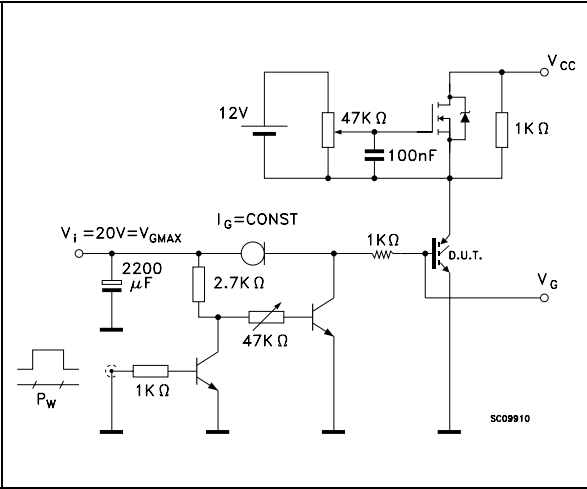
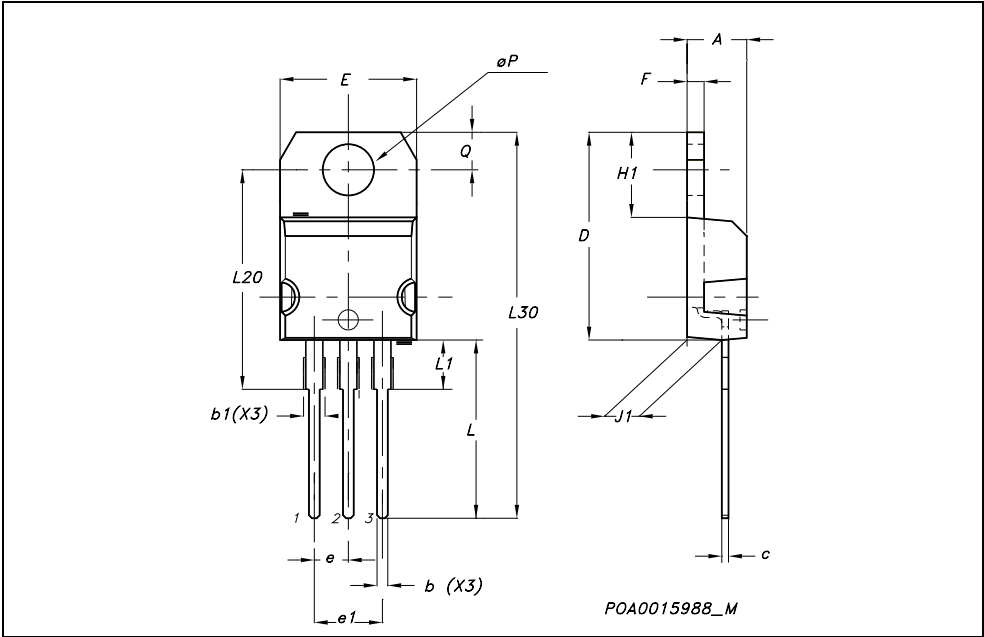


Figure 5: Gate Charge Test Circuit



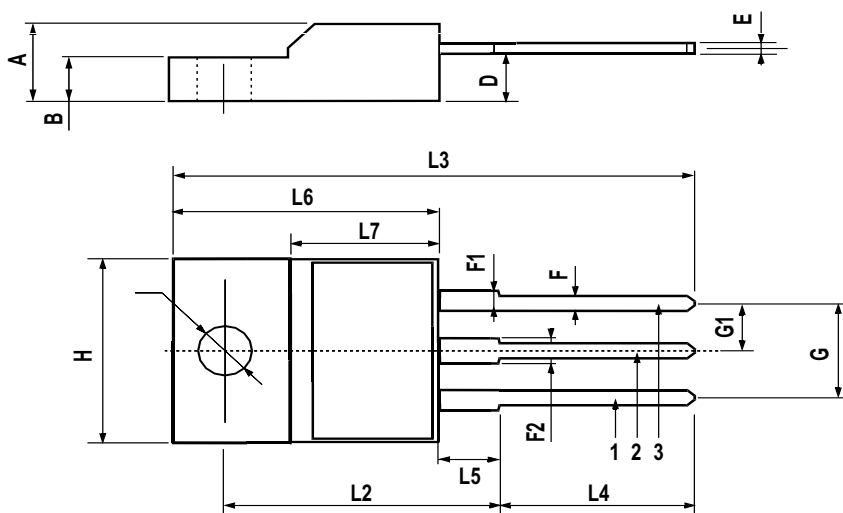
TO-220 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
b	0.61		0.88	0.024		0.034
b1	1.15		1.70	0.045		0.066
c	0.49		0.70	0.019		0.027
D	15.25		15.75	0.60		0.620
E	10		10.40	0.393		0.409
e	2.40		2.70	0.094		0.106
e1	4.95		5.15	0.194		0.202
F	1.23		1.32	0.048		0.052
H1	6.20		6.60	0.244		0.256
J1	2.40		2.72	0.094		0.107
L	13		14	0.511		0.551
L1	3.50		3.93	0.137		0.154
L20		16.40			0.645	
L30		28.90			1.137	
øP	3.75		3.85	0.147		0.151
Q	2.65		2.95	0.104		0.116



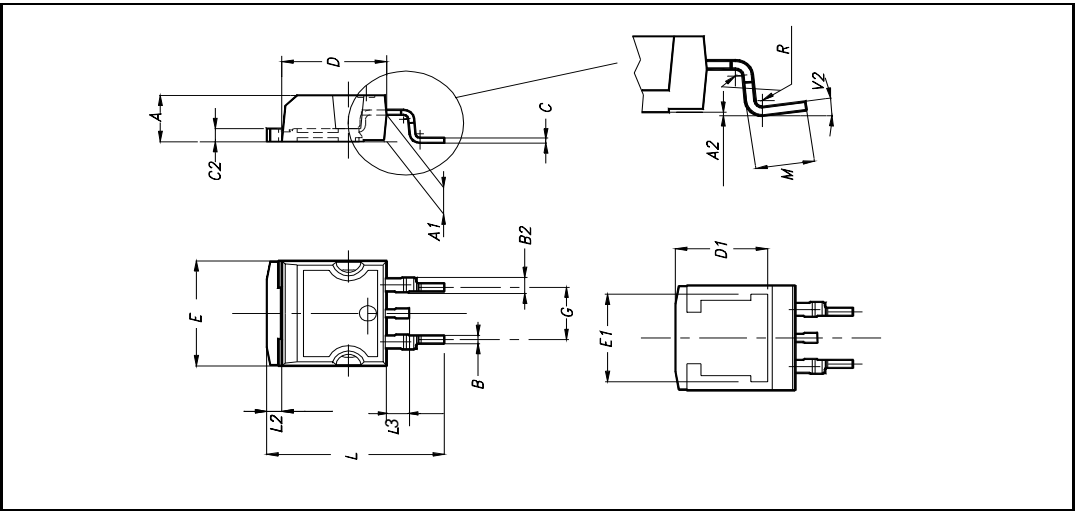
TO-220FP MECHANICAL DATA

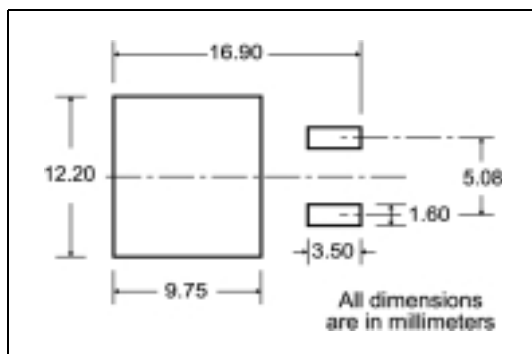
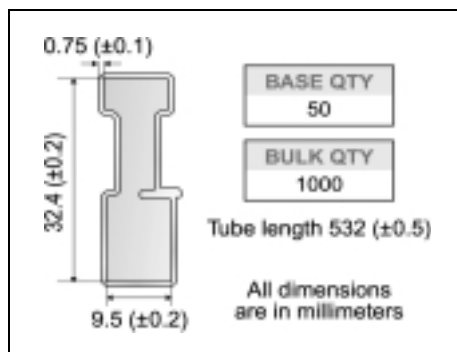
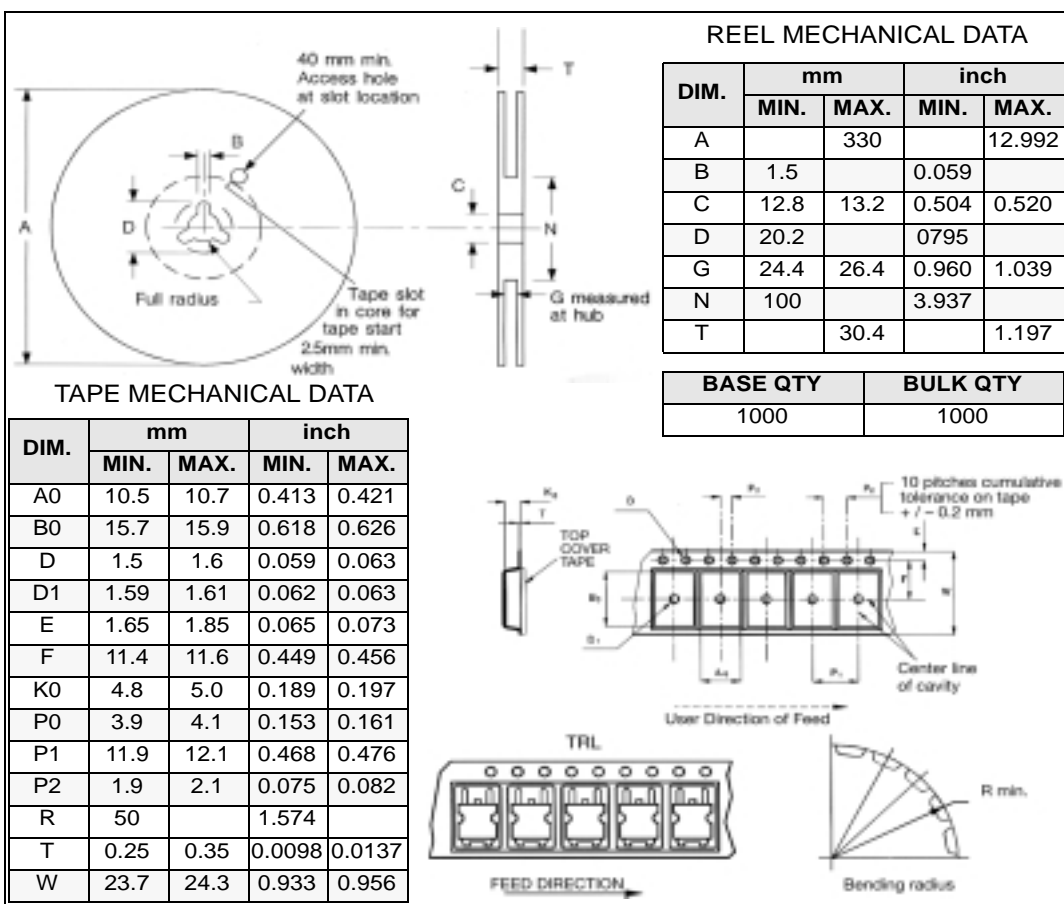
DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
B	2.5		2.7	0.098		0.106
D	2.5		2.75	0.098		0.108
E	0.45		0.7	0.017		0.027
F	0.75		1	0.030		0.039
F1	1.15		1.7	0.045		0.067
F2	1.15		1.7	0.045		0.067
G	4.95		5.2	0.195		0.204
G1	2.4		2.7	0.094		0.106
H	10		10.4	0.393		0.409
L2		16			0.630	
L3	28.6		30.6	1.126		1.204
L4	9.8		10.6	.0385		0.417
L5	2.9		3.6	0.114		0.141
L6	15.9		16.4	0.626		0.645
L7	9		9.3	0.354		0.366
Ø	3		3.2	0.118		0.126



D²PAK MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP	MAX.	MIN.	TYP.	MAX.
A	4.4		4.6	0.173		0.181
A1	2.49		2.69	0.098		0.106
A2	0.03		0.23	0.001		0.009
B	0.7		0.93	0.027		0.036
B2	1.14		1.7	0.044		0.067
C	0.45		0.6	0.017		0.023
C2	1.23		1.36	0.048		0.053
D	8.95		9.35	0.352		0.368
D1		8			0.315	
E	10		10.4	0.393		
E1		8.5			0.334	
G	4.88		5.28	0.192		0.208
L	15		15.85	0.590		0.625
L2	1.27		1.4	0.050		0.055
L3	1.4		1.75	0.055		0.068
M	2.4		3.2	0.094		0.126
R		0.4			0.015	
V2	0°		4°			



D²PAK FOOTPRINT**TUBE SHIPMENT (no suffix)*****TAPE AND REEL SHIPMENT (suffix "T4")***

* on sales type

Table 10: Revision History

Date	Revision	Description of Changes
14-Feb-2005	1	New release

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